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審査請求 未請求 発明の数 1 (全3頁)

⑮ 発明の名称 半導体ウェハの洗浄方法

⑯ 特 願 昭60-258064

⑰ 出 願 昭60(1985)11月18日

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明 細 書

1. 発明の名称 半導体ウェハの洗浄方法

2. 特許請求の範囲

(1) アンモニア、硫酸、塩酸等より成る洗浄液内に半導体ウェハを浸漬した後、前記洗浄液中にオゾンを供給することを特徴とする半導体ウェハの洗浄方法。

3. 発明の詳細な説明

(1) 産業上の利用分野

本発明は半導体ウェハの洗浄方法、特に洗浄中に酸素を供給する半導体ウェハの洗浄方法に関する。

(2) 従来の技術

従来、半導体ウェハの洗浄方法としては第2図に示す如く、洗浄槽3内に硫酸( $H_2SO_4$ )、アンモニア水( $NH_4OH$ )、塩酸( $HCl$ )、弗酸( $HF$ )等の10%以下の 釈液を洗浄液3として入れ、この洗浄液3をヒーター32で 80℃程度に加熱し、この液3内に半導体ウェハを浸漬して洗浄を行っている。洗浄の活性化を行うために半導体ウ

ェハの投入直前に過酸化水素( $H_2O_2$ )を洗浄液3に滴下して酸素を発生させて洗浄の均一化を図っている。

新る方法は例えば特開昭59-46032号公報(H01L21/304)等で公知である。

(1) 発明が解決しようとする問題点

しかしながら新る方法では種々の欠点が生じた。第1に過酸化水素を用いるため熱分解されて水が発生し、洗浄液3が更に希釈され洗浄にむらが生じて半導体ウェハの表面均一性が悪い欠点があった。このため熱酸化による酸化膜の欠陥密度が高くなったり、ポリシリコンの洗浄では表面状態にむらが生じる。

第2に過酸化水素を用いるためその液内に含まれるゴミで洗浄液3が汚れ、クリーンな洗浄を行えない欠点があった。

第3に洗浄液3の温度を上昇して洗浄効率を上げようとするとき過酸化水素の熱分解が進められてかえって洗浄効果が落ちる欠点があった。

(2) 問題点を解決するための手段

本発明は前記した欠点に鑑みてなされ、洗浄液中にオゾンを提供することにより従来の欠点を大巾に改良した半導体ウェハの洗浄方法を提供することである。

#### (III) 作用

本発明に依れば、洗浄時間中洗浄液(4)中にオゾンガスを注入しているので、酸度を一定量供給でき洗浄液(4)の希釈化も防止できる。

#### (IV) 実施例

本発明に依る半導体ウェハの洗浄方法を第1図を参照して詳述する。

洗浄槽(1)内に90～96%の過硫酸原液( $H_2SO_5$ )、アンモニア水( $NH_4OH$ )、塩酸( $HCl$ )、硝酸( $HNO_3$ )、弗酸( $HF$ )等の10%以下の希釈液を洗浄液(4)として入れ、この洗浄槽(1)下に多孔を有する石英又はテフロンより成るパイプ(2)を設けてオゾン( $O_3$ )が下から吹き出す様になっている。洗浄槽(1)の下にはヒーター(3)を設け、洗浄液(4)を加熱する。硫酸の場合は100～140℃に加熱し、アンモニア水の場合は80～100℃

に加熱している。

所る洗浄槽(1)内に器具に収納した半導体ウェハを浸漬し、パイプ(2)よりオゾンを注入して酸液イオンを洗浄液(4)内に供給しながら半導体ウェハの洗浄を行う。

所る方法に依れば、オゾンが気体であるので洗浄液(4)の希釈化を伴わずに酸液イオンを供給し続ける。これにより洗浄液の酸化を促進して流水処理を行なえるので極めてクリーンな洗浄を安定して行なうことができる。

第3図に本発明と従来の洗浄方法の洗浄効果を説明する特性図を示す。従来のRCA洗浄法と呼ばれる $NH_4OH + H_2O$ と本発明の $NH_4OH + O_3$ とを比較すると、従来の加熱温度が $H_2O$ の臨分界より80～90℃に保たれ、 $H_2O \rightarrow H_2O + O_3 \uparrow$ の熱分解により発生する水により液希釈が生じて矢印の様に洗浄効果が劣化しているのに対し、本発明ではオゾンを用いるため100℃以上に加熱でき洗浄効果を大巾に向上できる。また従来の $H_2SO_4 + H_2O$ と本発明の

$H_2SO_4 + O_3$ についても同様の効果が得られる。

#### (V) 発明の効果

本発明に依れば、第1にオゾンで酸液イオン発生部として用いるので洗浄液(4)が希釈化されず、酸液イオンで洗浄が活性化され半導体ウェハの表面を均一に且つ安定して洗浄できる利点を有する。

第2にオゾンは気体であるので注入しても洗浄液(4)がゴミ等で汚染されるおそれなくなり、クリーンな洗浄ができる利点を有する。

第3にオゾンを用いるので洗浄液(4)の温度を $H_2O$ の熱分解に無関係に上げて酸液イオンを一定量供給でき、洗浄効果を従来の2倍以上に向上できる利点を有する。

第4にオゾンを用いるので $H_2O$ を用いる場合に比べて $H_2O$ の液の管理が不要となり安全上の利点が容易となる利点を有する。

#### 4. 図面の簡単な説明

第1図は本発明に依る半導体ウェハの洗浄方法を説明する断面図、第2図は従来の半導体ウェハ

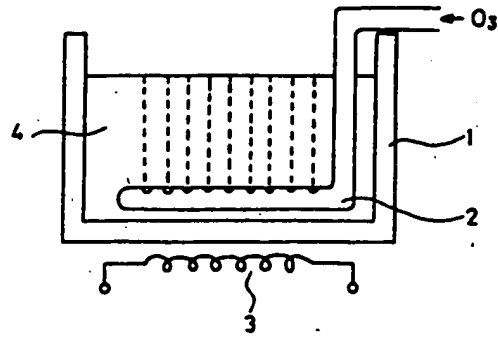
の洗浄方法を説明する断面図、第3図は本発明と従来の洗浄効果を説明する曲線図である。

(1)は洗浄槽、(2)はパイプ、(3)はヒーター、(4)は洗浄液である。

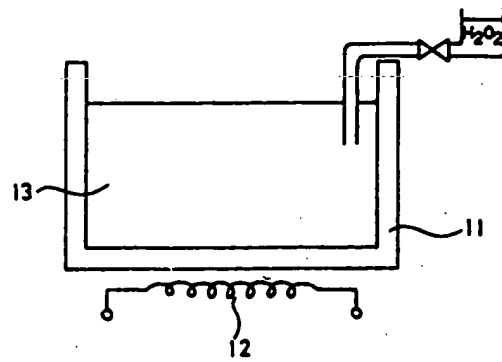
出願人 三洋電機株式会社 外1名

代理人 弁理士 佐野 勝 夫

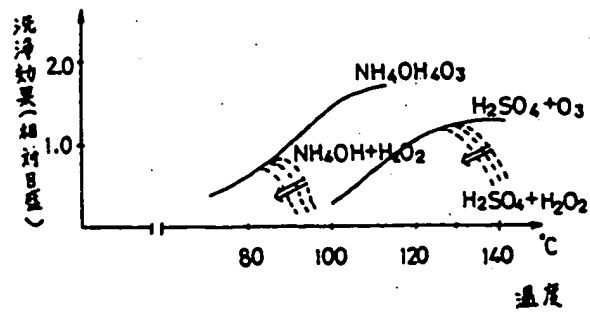
第 1 图



第 2 图



第 3 图



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WADA et al

Reference No.

Job No: TOT-LYON-2288A

19. Japan Patent Office (JP) 11. Patent Application Laid-open No.

12. Japan Laid-open Patent Gazette (A) Showa 62-117330(1987)

51. Int. Cl.<sup>3</sup>  
H 01 LJ 21/304  
B 08 B 21/304

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D-7446-4F

Z-6420-3B

43. Patent Laid-open Date: May 28, 1987 (Showa 62)

Place for Technology Labeling

Request for Examination: Attached / Not Requested (Number of Claims: 1 (Total 3 pages))

54. Title of Invention	Semiconductor Wafer Cleaning Method
21. Application No.	Showa 60-258064
22. Date of Filing	November 18, 1985 (Showa 60)
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72. Inventor	Norio Koide 18, Oaza-Sakada, Oizumi-cho, Ouragun, Gunma-ken Tokyo Sanyo Electric Co., Ltd
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74. Agent	Takushi Nishino, Patent Attorney, and one additional person

## SPECIFICATION

1. Title of the invention Semiconductor Wafer Cleaning Method

## 2. Claims

(1) A semiconductor wafer cleaning method, characterized in that a semiconductor wafer is immersed in a cleaning liquid composed of ammonia, sulfuric acid, hydrochloric acid or other substance, whereupon ozone is supplied to the aforementioned cleaning liquid.

## 3. Detailed description of the invention

## Field of industrial utilization

The present invention concerns a method for cleaning semiconductor wafers, and in particular, concerns a method for cleaning semiconductor wafers wherein oxygen is supplied during cleaning.

## Prior art

In the past, methods for cleaning semiconductor wafers, as shown in Figure 2, have involved introducing a dilute solution containing 10% or less of such substances as sulfuric acid ( $H_2SO_4$ ), aqueous ammonia ( $NH_4OH$ ), hydrochloric acid ( $HCl$ ) and hydrofluoric acid ( $HF$ ) into a cleaning vessel 11, and heating this cleaning liquid 13 to approximately  $80^\circ C$  with a heater 12. The semiconductor wafer is cleaned by immersing it in this liquid 13. In order to improve the cleaning activity, hydrogen peroxide ( $H_2O_2$ ) is added dropwise to the cleaning liquid 13 immediately prior to introduction of the semiconductor wafer so that oxygen is generated, thereby achieving greater cleaning uniformity.

<sup>1</sup> ILS Note - An alternative way of reading this person's name is Hiroshi.



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This type of method is common knowledge in, for example, Japanese Unexamined (Kokai) Patent Application No. Sho 59-46032 (H 01 L 21/304).

## Problems to be solved by the invention

However, various disadvantages have resulted from the type of method described above. Firstly, there is the disadvantage that water is generated due to thermal decomposition resulting from the use of hydrogen peroxide, and the cleaning liquid 13 is thus additionally diluted, producing non-uniform cleaning which results in a loss of surface uniformity of the semiconductor wafer. For this reason, the defect density of oxide films formed by thermal oxidation increases, and the surface condition becomes non-uniform during polysilicon cleaning.

Secondly, there is the disadvantage that the cleaning liquid 13 is contaminated by contaminants contained in the liquid because hydrogen peroxide is used, so that a clean cleaning process is not carried out.

Thirdly, if the attempt is made to improve cleaning efficiency by increasing the temperature of the cleaning liquid 13, there is the disadvantage that thermal decomposition of the hydrogen peroxide will accelerate, and the cleaning effects will actually be compromised.

## Means for solving the problems

The present invention was developed in light of the disadvantages described above, and offers a cleaning method for semiconductor wafers wherein past disadvantages have been dramatically mitigated by means of supplying ozone to the cleaning liquid.

## Action

In accordance with the present invention, ozone gas is introduced into the cleaning liquid 4 during cleaning, so that oxygen can be supplied in constant quantities and dilution of the cleaning liquid 4 can be stopped.

## Working examples

The cleaning method for semiconductor wafers pertaining to the present invention is described below in reference to Figure 1.

A 90-96% concentrated sulfuric acid stock solution ( $H_2SO_4$ ), ammonia aqueous solution ( $NH_4OH$ ), hydrochloric acid ( $HCl$ ), nitric acid ( $HNO_3$ ) or hydrofluoric acid ( $HF$ ) is diluted to 10% or less and is introduced as cleaning liquid 4 into a cleaning vessel 1, where a pipe 2 composed of quartz or Teflon is installed below the cleaning vessel 1 in such a manner that ozone ( $O_3$ ) is blown upwards from below. A heater 3 is installed below the cleaning vessel 1 for heating the cleaning liquid 4. With sulfuric acid, heating is performed at 100-140°C, whereas with ammonia aqueous solution, heating is performed at 80-100°C.

A semiconductor wafer that is held on a stand is immersed in this cleaning vessel 1, and ozone is introduced from the pipe 2 so that the semiconductor wafer is cleaned while supplying oxygen ions into the cleaning liquid 4.

In this method, oxygen ions are continuously supplied without accompanying dilution of the cleaning liquid 4 because ozone is a gas. By this means, oxidation of the cleaned surface is facilitated and a hydrophilic treatment is carried out, so that an extremely clean cleaning process can be performed with good reliability.

Characteristic curves used for representing cleaning effects in the cleaning method of the present invention and a conventional cleaning method are shown in Figure 3. In comparing the method of the present invention wherein  $NH_4OH + O_3$  is used and a method known as a conventional RCA cleaning method wherein  $NH_4OH + H_2O_2$  is used, the heating temperature has been restricted to 80-90°C in the past due to thermal decomposition of the  $H_2O_2$ , and the cleaning effects deteriorate as indicated by the arrow due to dilution of the liquid with water generated by thermal decomposition:  $H_2O_2 \rightarrow H_2O + O_2$  upwards arrow. With the present invention, however, ozone is used so that cleaning effects are greatly improved because heating can be performed at 100°C or greater. In addition, the method of the present invention that employs  $H_2SO_4 + O_3$  provides effects that are similar to those of conventional methods that employ  $H_2O_4 + H_2O_2$ .

## Effect of the invention

Firstly, the present invention has the advantage that ozone is used as the source for generating oxygen ions, so that the cleaning liquid 4 is not diluted, and cleaning is activated by the oxygen ions. As a result, cleaning can be reliably and uniformly carried out at the surface of the semiconductor wafer.

Secondly, the invention has the advantage that ozone is a gas, and thus there is no danger of pollution of the cleaning liquid 4 with contaminants when this substance is introduced, so that cleaning can be performed



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without contamination.

Thirdly, the invention has the advantage that, because ozone is used, oxygen ions can be supplied in constant amounts even if the temperature of the cleaning liquid 4 is increased, because there is no connection with thermal degradation of  $H_2O_2$ . The cleaning effects can thus be increased by two or more times over past methods.

Fourthly, the invention has the advantage that, because ozone is used,  $H_2O_2$  liquid need not be managed, which simplifies management from the standpoint of safety relative to cases where  $H_2O_2$  is used.

Brief description of the figures

Figure 1 is a cross-sectional diagram describing the cleaning method for semiconductor wafers pertaining to the present invention, Figure 2 is a cross-sectional diagram describing a conventional method for cleaning semiconductor wafers, and Figure 3 is a graph for showing the cleaning effects obtained in the past and with the present invention.

- 1 Cleaning vessel
- 2 Pipe
- 3 Heater
- 4 Cleaning liquid

Figure 1

Figure 2

Figure 3

- 1 Cleaning effects (relative scale)
- 2 Temperature



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AN - 87-117330  
TI - WASHING METHOD R SEMICONDUCTOR WAFER  
PA - (2000188) SA ELECTRIC CO LTD  
IN - WADA, TOSHIO; KOIDE, NORIO

PN - 87.05.28 JP62117330, JP 62-117330

AP - 85.11.18 85JP-258064, 60-258064

SO - 87.10.27 SECT. E, SECTION NO. 552; VOL. 11, NO. 329, PG. 141.

IC - H01L-021/304; B08B-003/10

JC - 42.2 (ELECTRONICS--Solid State Components); 28.1 (SANITATION--Sanitary Equipment)

AB - PURPOSE: To wash a wafer surface uniformly and stably without diluting a washing by injecting ozone gas into the washing during the washing time. CONSTITUTION: A diluted solution, such as 90-96% H(sub 2)SO(sub 4), NH(sub 4)OH, HCl, etc. is introduced into a washing tank 1 as a washing

4 while a pipe 2 consisting of quartz, Teflon, etc. with a large number of holes is mounted to a lower section in the tank 1 and ozone can be fed.

A heater 3 is installed to the lower section of the tank 1, and the liquid 4 is heated. Semiconductor wafers housed in a jig are dipped into the tank 1, ozone is injected from the pipe 2, and the semiconductor wafers are washed, feeding oxygen ions to the liquid 4. Accordingly, since

ozone is a gas, the liquid 4 is not diluted, and the oxidation of a washing surface is accelerated and hydrophilic treatment is executed, thus

stably conducting extremely clean washing.

SS 24?

( $H_2SO_4 - H_2O - O_3$   
 $NH_4OH - H_2O - O_3$  or  
 $HCl - H_2O - O_3$ )

-9- (WPAT)

AN - 87-188360/27

TI - Appts. for cleaning semiconductor wafer - supplies ozone into washings composed of ammonia, sulphuric acid, and hydrochloric acid during cleaning NoAbstract Dwg 1/3

DC - L03 P43 U11

PA - (SAOL) SANYO ELECTRIC CO; (TOKR) TOKYO SANYO ELECTRIC CO

PR - 85.11.18 85JP-258064

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8p

AP -- 85JP-258064 85.11.18

IC2 - B08B-003/10 H01L-021/30

102-82-85,88-90

JP